Phase Control Thyristors (Stud Version), 230 A

TO-93 (TO-209AB)

FEATURES

- Center amplifying gate
- International standard case TO-93 (TO-209AB)
- Hermetic metal case with ceramic insulator
- Compression bonded encapsulation for heavy duty operations such as severe thermal cycling
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

Pb-free
RoHS
COMPLIANT

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

PRIMARY CHARACTERISTICS	
$I_{T(AV)}$	230 A
V_{DRM}/V_{RRM}	1400 V, 1600 V
V_{TM}	1.55 V
I_{GT}	150 mA
T_J	-40 °C to +125 °C
Package	TO-93 (TO-209AB)
Circuit configuration	Single SCR

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		230	A
	T_C	85	°C
$I_{T(RMS)}$		360	A
I_{TSM}	50 Hz	5700	A
	60 Hz	5970	
I^2t	50 Hz	163	kA²s
	60 Hz	149	
V_{DRM}/V_{RRM}		1400 to 1600	V
t_q	Typical	100	μs
T_J		-40 to +125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS

TYPE NUMBER	VOLTAGE CODE	V_{DRM}/V_{RRM}, MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V_{RSM}, MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
VS-ST230S	14	1400	1500	30
	16	1600	1700	

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current at case temperature	$I_{T(AV)}$	180° conduction, half sine wave			230	A
					85	°C
Maximum RMS on-state current	$I_{T(RMS)}$	DC at 78 °C case temperature			360	A
Maximum peak, one-cycle non-repetitive surge current	I_{TSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	5700	
		t = 8.3 ms			5970	
		t = 10 ms	100 % V_{RRM} reapplied		4800	
		t = 8.3 ms			5000	
Maximum I^2t for fusing	I^2t	t = 10 ms	No voltage reapplied		163	kA^2s
		t = 8.3 ms			148	
		t = 10 ms	100 % V_{RRM} reapplied		115	
		t = 8.3 ms			105	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 to 10 ms, no voltage reapplied			1630	$kA^2\sqrt{s}$
Low level value of threshold voltage	$V_{T(TO)1}$	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum			0.92	V
High level value of threshold voltage	$V_{T(TO)2}$	($I > \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum			0.98	
Low level value of on-state slope resistance	r_{t1}	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum			0.88	mΩ
High level value of on-state slope resistance	r_{t2}	($I > \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum			0.81	
Maximum on-state voltage	V_{TM}	I_{pk} = 720 A, $T_J = T_J$ maximum, t_p = 10 ms sine pulse			1.55	V
Maximum holding current	I_H	T_J = 25 °C, anode supply 12 V resistive load			600	mA
Maximum (typical) latching current	I_L				1000 (300)	

SWITCHING

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dI/dt	Gate drive 20 V, 20 Ω, $t_r \leq 1$ µs $T_J = T_J$ maximum, anode voltage ≤ 80 % V_{DRM}	1000	A/µs
Typical delay time	t_d	Gate current 1 A, dI_g/dt = 1 A/µs V_d = 0.67 % V_{DRM}, T_J = 25 °C	1.0	µs
Typical turn-off time	t_q	I_{TM} = 300 A, $T_J = T_J$ maximum, dI_F/dt = 20 A/µs, V_R = 50 V, dV/dt = 20 V/µs, gate 0 V 100 Ω, t_p = 500 µs	100	

BLOCKING

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I_{RRM}, I_{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	30	mA

TRIGGERING

PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
				TYP.	MAX.	
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms		10.0		W
Maximum average gate power	$P_{G(AV)}$	$T_J = T_J$ maximum, f = 50 Hz, d% = 50		2.0		
Maximum peak positive gate current	I_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms		3.0		A
Maximum peak positive gate voltage	$+ V_{GM}$	$T_J = T_J$ maximum, $t_p \leq 5$ ms		20		V
Maximum peak negative gate voltage	$- V_{GM}$			5.0		
DC gate current required to trigger	I_{GT}	$T_J = - 40$ °C	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units 12 V anode to cathode applied	180	-	
		$T_J = 25$ °C		90	150	mA
		$T_J = 125$ °C		40	-	
DC gate voltage required to trigger	V_{GT}	$T_J = - 40$ °C		2.9	-	V
		$T_J = 25$ °C		1.8	3.0	
		$T_J = 125$ °C		1.2	-	
DC gate current not to trigger	I_{GD}	$T_J = T_J$ maximum	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V_{DRM} anode to cathode applied	10		mA
DC gate voltage not to trigger	V_{GD}			0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating junction temperature range	T_J		-40 to 125	°C
Maximum storage temperature range	T_{Stg}		-40 to 150	
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	0.10	K/W
Maximum thermal resistance, case to heatsink	R_{thC-hs}	Mounting surface, smooth, flat and greased	0.04	
Mounting torque, ± 10 %		Non-lubricated threads	31 (275)	N · m (lbf · in)
		Lubricated threads	24.5 (210)	
Approximate weight			280	g
Case style		See dimensions - link at the end of datasheet	TO-93 (TO-209AB)	

ΔR_{thJC} CONDUCTION

CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.016	0.012	$T_J = T_J$ maximum	K/W
120°	0.019	0.020		
90°	0.025	0.027		
60°	0.036	0.037		
30°	0.060	0.060		

Note

- The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

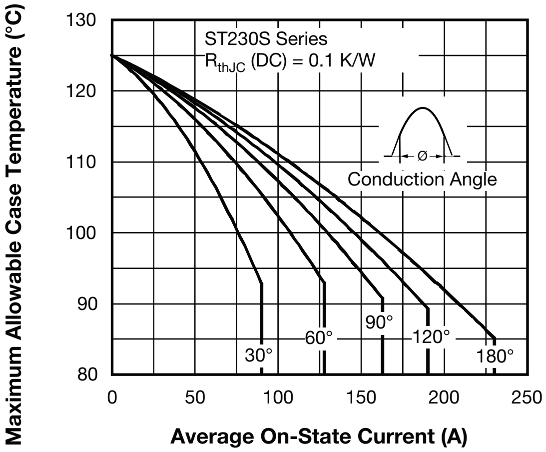


Fig. 1 - Current Ratings Characteristics

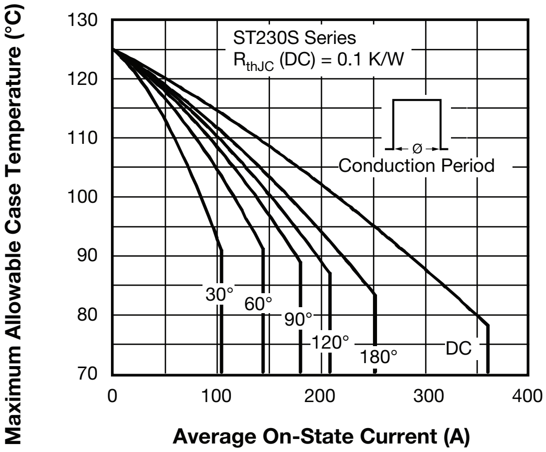


Fig. 2 - Current Ratings Characteristics

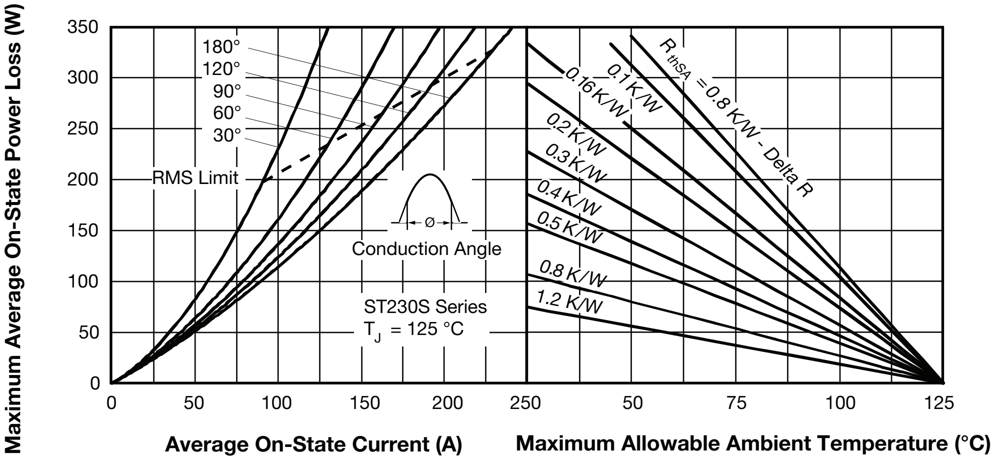


Fig. 3 - On-State Power Loss Characteristics

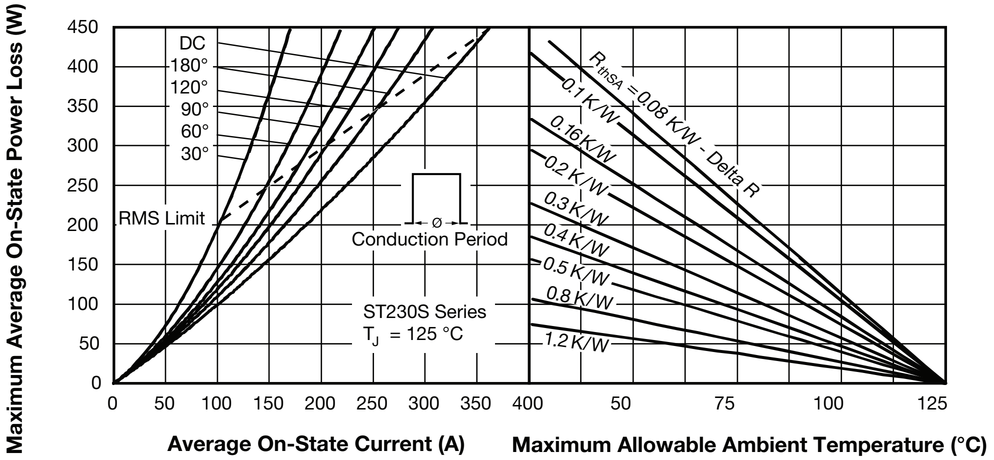


Fig. 4 - On-State Power Loss Characteristics

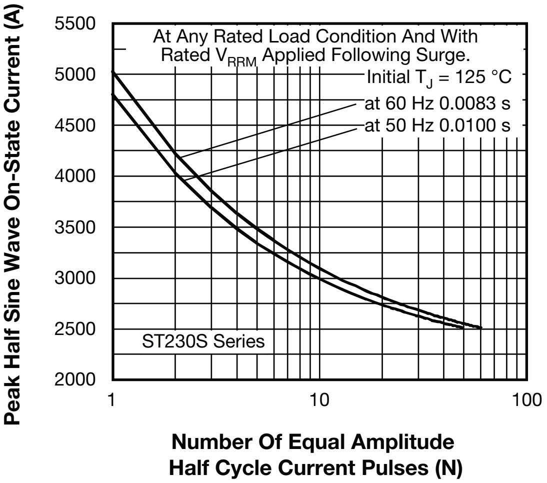


Fig. 5 - Maximum Non-Repetitive Surge Current

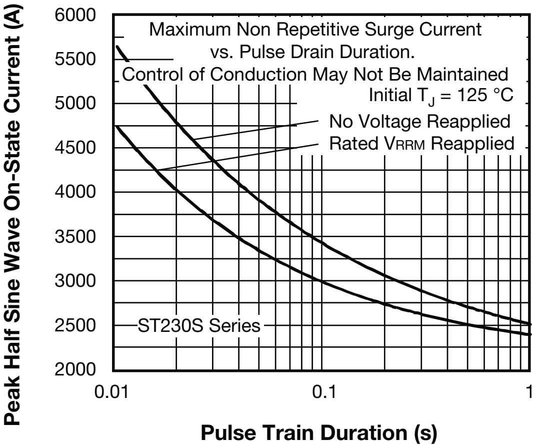


Fig. 6 - Maximum Non-Repetitive Surge Current

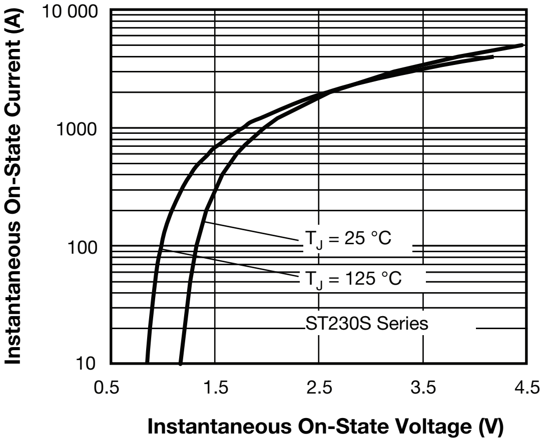


Fig. 7 - On-State Voltage Drop Characteristics

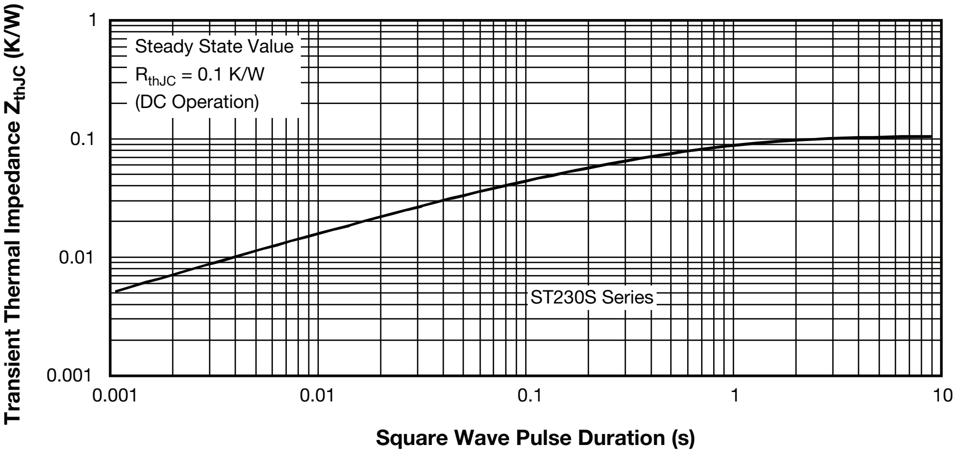


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

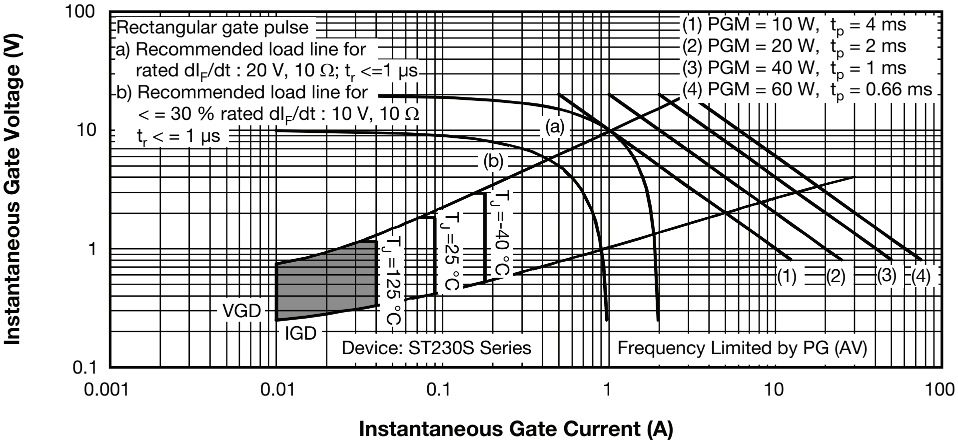


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	ST	23	0	S	16	P	0	PbF
	①	②	③	④	⑤	⑥	⑦	⑧	⑨

1 - Vishay Semiconductors product
2 - Thyristor
3 - Essential part number
4 - 0 = converter grade
5 - S = compression bonding stud
6 - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)
7 - P = stud base 3/4"-16UNF2A threads
8 - 0 = eyelet terminals (gate and auxiliary cathode leads)
1 = fast-on terminals (gate and auxiliary cathode leads)
9 - None = standard production
\- PbF = lead (Pb)-free

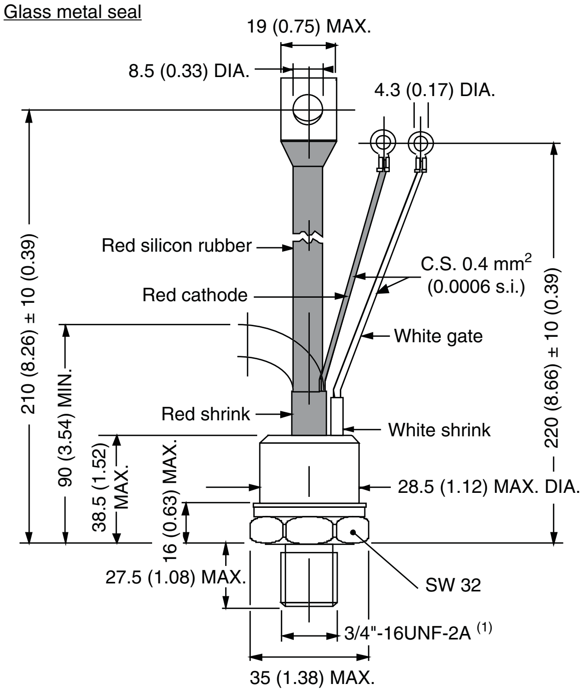
Note: For metric device M16 x 1.5 contact factory

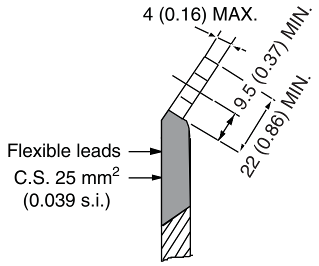
LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95082

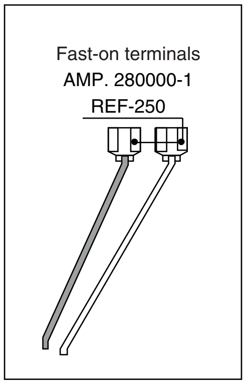
TO-209AB (TO-93)

DIMENSIONS in millimeters (inches)

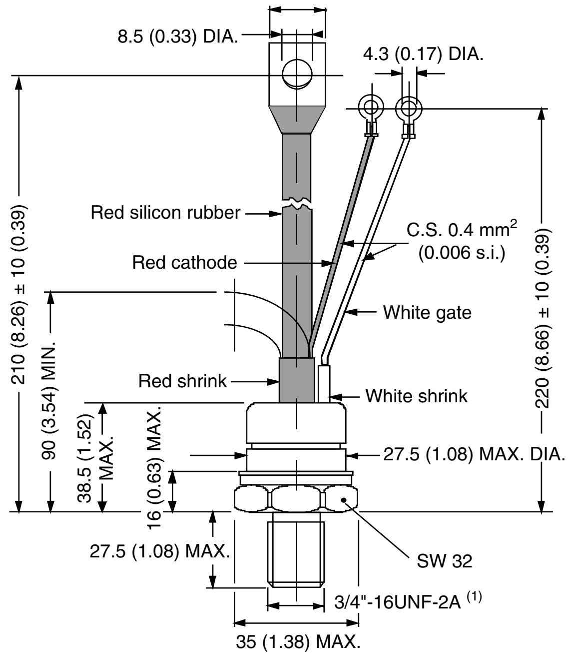
Glass metal seal

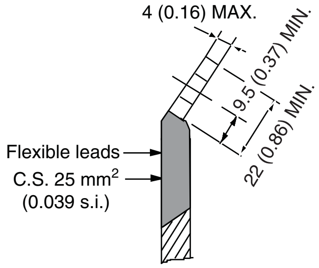






Ceramic housing





Note

(1) For metric device: M16 x 1.5 - length 21 (0.83) maximum

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